

# Wafer

N-type

M10-Res0.4~1.6-A



TOP PV TECH,  
DRIVING ONWARD FOR GREEN ENERGY

# Monocrystalline Silicon Wafer Specification

N-type-M10-Res 0.4~1.6-Grade A

## Key Parameters

Conductive Type	N-type	P/N Type Tester (DLY – 2 P/N)
Doping Element	Phos. (Phosphorus)	--
Resistivity/ $\Omega \cdot \text{cm}$	0.4~1.6	Silicon Wafer Automatic Testing Equipment
Minority Carrier Lifetime/ $\mu\text{s}$	$\geq 1000$	Transient Photoconductance Decay Method
Interstitial Oxygen Content/ $\text{at}/\text{cm}^3$	$\leq 6.0 \times 10^{17}$	Fourier Transform Infrared Spectrometer (ASTM F121–83)
Substitutional Carbon Content/ $\text{at}/\text{cm}^3$	$\leq 5.0 \times 10^{16}$	Fourier Transform Infrared Spectrometer (GB/T1558–2009)

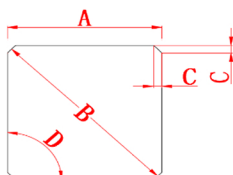
## Material Properties

Growth Method	Czochralski Method	--
Crystallinity	Single Crystal	--
Dislocation Density/ $\text{pcs}/\text{cm}^2$	$\leq 500$	Preferred Chemical Etching Method (ASTM F47–88)
Surface Crystal Orientation/ $^\circ$	$<100> \pm 3$	X-ray Diffractometer (ASTM F26–1987)
Side Crystal Orientation/ $^\circ$	$<010>, <001> \pm 3$	X-ray Diffractometer (ASTM F26–1987)

## Geometric Dimensions and Surface Properties

Silicon Wafer Model	M10	--
Geometric Shape	Standard	--
Chamfered Edge Shape	Rounded	--
Silicon Wafer Edge Distance/mm	$182.2 \pm 0.25$	Silicon Wafer Automatic Testing Equipment
Silicon Wafer Diameter/mm	$\Phi 247 \pm 0.25$	Silicon Wafer Automatic Testing Equipment
Arc Length Projection/mm	$7.72 \pm 0.5$	Silicon Wafer Automatic Testing Equipment
Perpendicularity/ $^\circ$	$90 \pm 0.15$	Silicon Wafer Automatic Testing Equipment
Thickness/ $\mu\text{m}$	$130 \pm 8$	Silicon Wafer Automatic Testing Equipment
Batch Thickness/ $\mu\text{m}$	$\geq 130$	Silicon Wafer Automatic Testing Equipment
TTV/ $\mu\text{m}$	$\leq 20$	Silicon Wafer Automatic Testing Equipment
Scratch/ $\mu\text{m}$	$\leq 13$	Silicon Wafer Automatic Testing Equipment
Warpage/ $\mu\text{m}$	$\leq 40$	Silicon Wafer Automatic Testing Equipment
Bow/ $\mu\text{m}$	$\leq 40$	Silicon Wafer Automatic Testing Equipment
Cutting Method	Diamond Wire Cutting	--
Surface Quality	The surface is clean, with no visible pollution, and color deviation (judged according to standard sample pieces)	Silicon Wafer Automatic Testing Equipment
Edge Chipping	Depth $\leq 0.3\text{mm}$ & Length $\leq 0.5\text{mm}$ , no more than 1 piece, no V – shaped edge chipping	Manual Inspection or Silicon Wafer Automatic Testing Equipment
Hidden Cracks/Pores	Not Allowed	Silicon Wafer Automatic Testing Equipment

Schematic diagram of silicon wafer dimensions



Size: M10  
 A:  $182.2 \pm 0.25\text{mm}$   
 B:  $\Phi 247 \pm 0.25\text{mm}$   
 C:  $7.72 \pm 0.5\text{mm}$   
 D:  $90 \pm 0.15^\circ$